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Power Matters[™]

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Overview Diagrams

Electrical Rating	Symbol	Min	Тур	Max	Unit
Collector to Emitter Saturation Voltage	V _{CE(sat)}			1.50	V
DC Current Gain	HFE	40.00		150.00	

Maximum Electrical Rating	Symbol	Min	Тур	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	V _{BR(CBO)}			300.00	V
Collector Current (dc)	I _C			30.00	Α
Collector-Emitter Voltage (Base Open)	V _{CEO}			200.00	V
Emitter-Base Voltage (Collector Open)	V _{EBO}			5.00	V
Power Dissipation, Total	P _T			350.00	W

This part can be found in the following product categories:

- Discretes ► Transistors ► BJT(BiPolar Junction Transistor) ► PNP Transistor
- Non-Radiation Hardened Devices ➤ Transistors ➤ BJT(BiPolar Junction Transistor) ➤ NPN Transistor

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